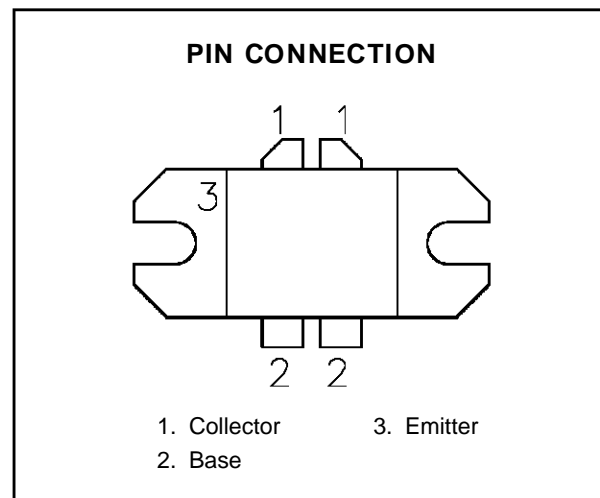
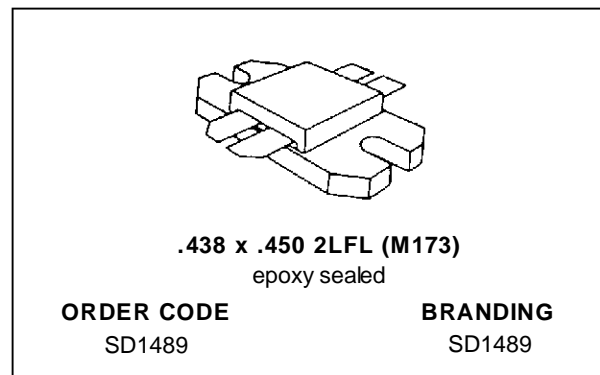


**RF & MICROWAVE TRANSISTORS
TV/LINEAR APPLICATIONS**

- 470 - 860 MHz
- 28 VOLTS
- CLASS AB PUSH PULL
- DESIGNED FOR HIGH POWER LINEAR OPERATION
- HIGH SATURATED POWER CAPABILITY
- GOLD METALLIZATION
- DIFFUSED EMITTER BALLAST RESISTORS
- COMMON EMITTER CONFIGURATION
- INTERNAL INPUT MATCHING
- P_{OUT} = 50 W MIN. WITH 6.5 dB GAIN


DESCRIPTION

The SD1489 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class AB operation in UHF and Band IV, V television transmitters and transposers.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	45	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _c	Device Current	8	A
P _{DISS}	Power Dissipation	175	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	1.0	°C/W
----------------------	----------------------------------	-----	------

SD1489**ELECTRICAL SPECIFICATIONS** ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_C = 50\text{mA}$	$I_E = 0\text{mA}$	45	—	—	V
BV_{CER}	$I_C = 20\text{mA}$	$R_{BE} = 10\Omega$	40	—	—	V
BV_{CEO}	$I_C = 200\text{mA}$	$I_B = 0\text{mA}$	30	—	—	V
BV_{EBO}	$I_E = 10\text{mA}$	$I_C = 0\text{mA}$	3.0	—	—	V
I_{CEO}	$V_{CE} = 28\text{V}$	$I_E = 0\text{mA}$	—	—	5	mA
h_{FE}	$V_{CE} = 5\text{V}$	$I_C = 3\text{A}$	10	—	80	—

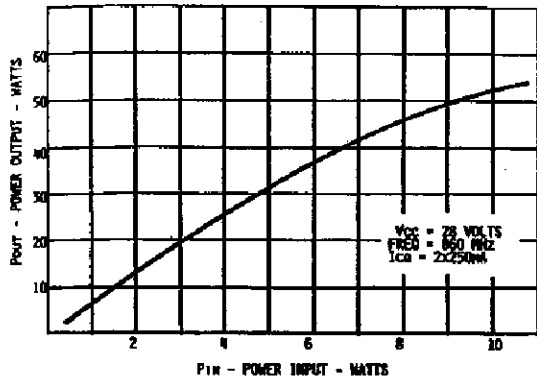
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 860\text{ MHz}$	$V_{CE} = 28\text{ V}$	$I_{CQ} = 2 \times 250\text{ mA}$	50	—	—	W
G_P	$f = 860\text{ MHz}$	$V_{CE} = 28\text{ V}$	$I_{CQ} = 2 \times 250\text{ mA}$	6.8	—	—	dB
η_C	$f = 860\text{ MHz}$	$V_{CE} = 28\text{ V}$	$I_{CQ} = 2 \times 250\text{ mA}$	—	45	—	%
C_{OB}	$f = 1\text{ MHz}$	$V_{CB} = 28\text{ V}$		—	70	—	pF

Note: Pulse Width = 10 μ Sec, Duty Cycle = 1%

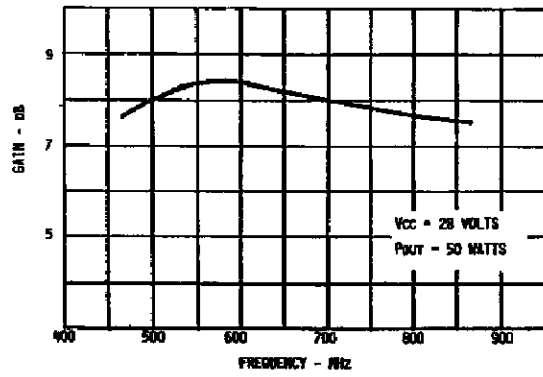
TYPICAL PERFORMANCE

OUTPUT POWER vs POWER INPUT



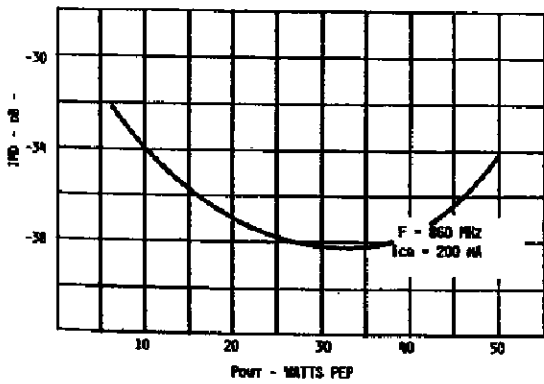
S88-SD1489-02

BROADBAND POWER GAIN vs FREQUENCY



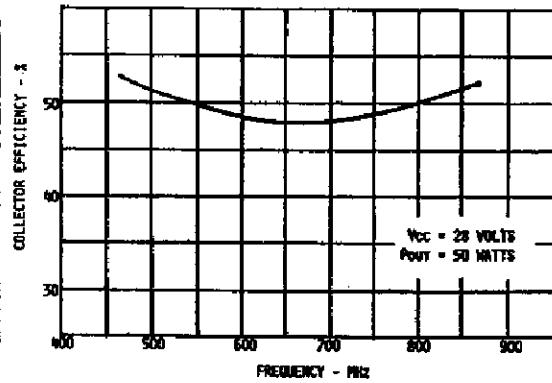
S88-SD1489-03

INTERMODULATION DISTORTION vs OUTPUT POWER



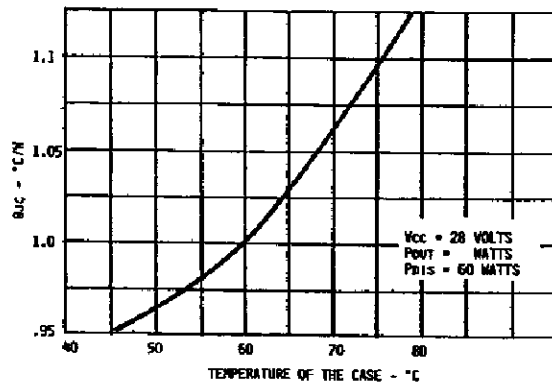
S88-SD1489-04

COLLECTOR EFFICIENCY vs FREQUENCY



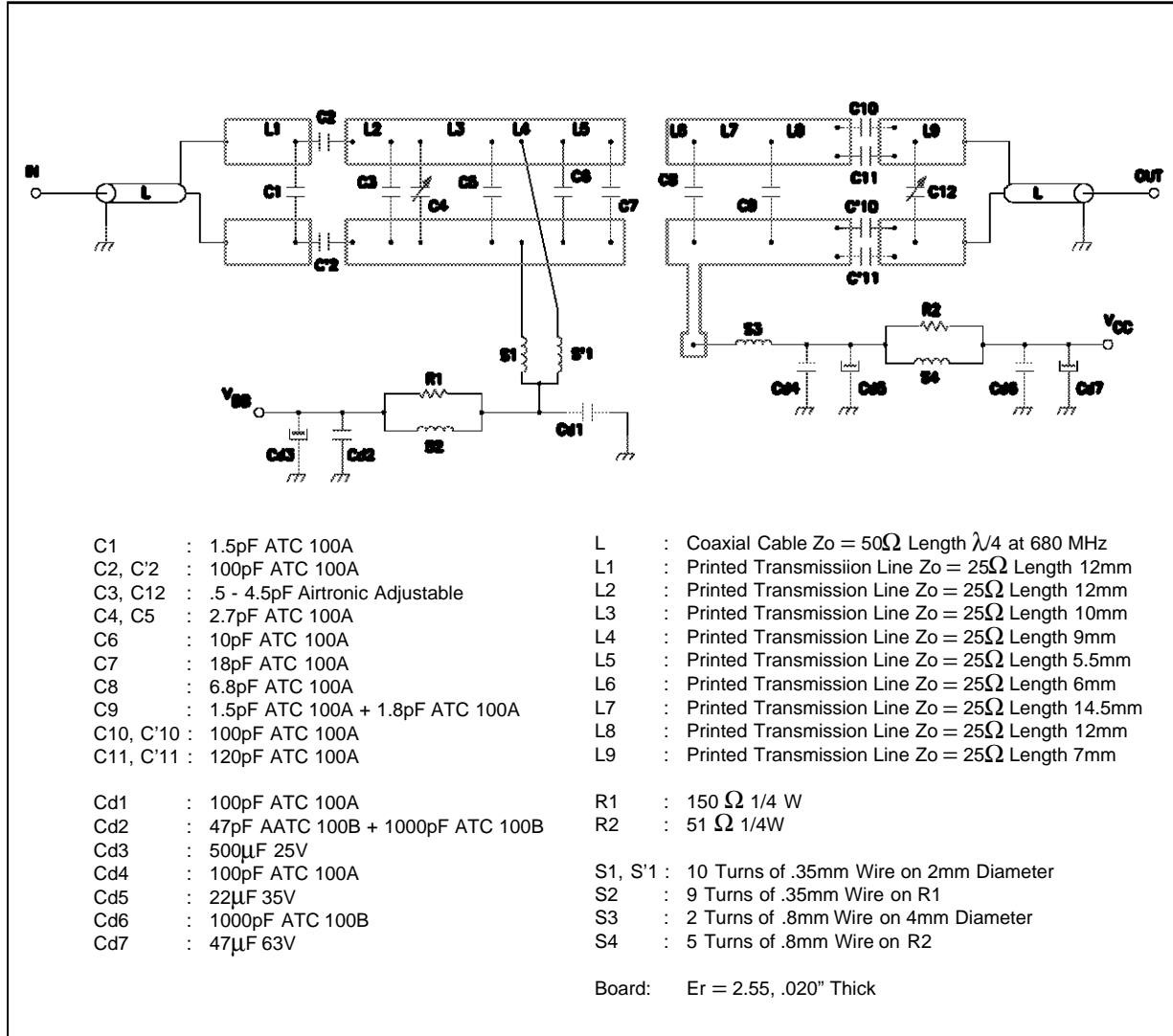
S88-SD1489-05

THERMAL RESISTANCE vs CASE TEMPERATURE

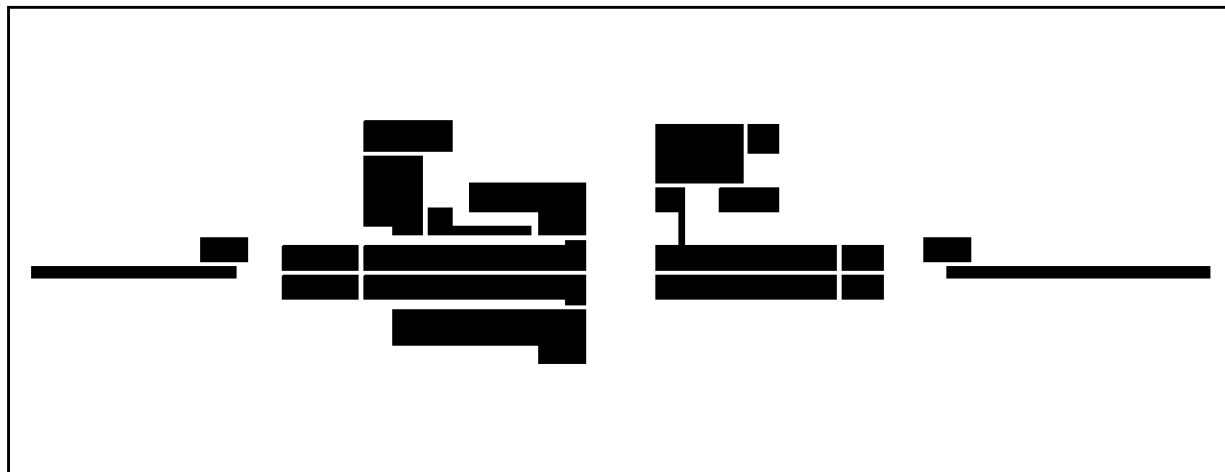


S88-SD1489-06

TEST CIRCUIT

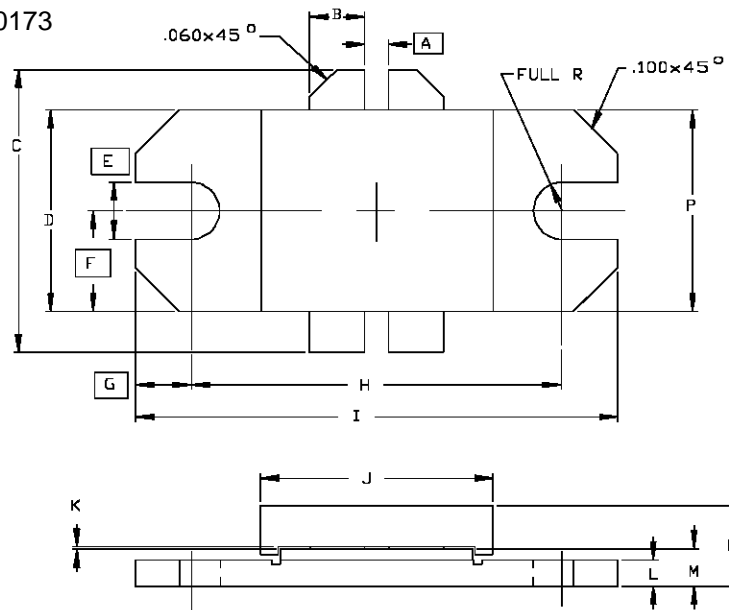


TEST CIRCUIT LAYOUT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0173



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.055/1,40		K	.002/0,05	.006/0,15
B	.120/3,05	.130/3,30	L	.055/1,40	.065/1,65
C		.785/19,94	M	.080/2,03	.095/2,41
D	.455/11,56	.465/11,81	N		.195/4,95
E	.125/3,18		P	.455/11,56	.465/11,81
F	.230/5,84				
G	.128/3,25				
H	.838/21,28	.850/21,59			
I	1.095/27,81	1.105/28,07			
J	.525/13,34	.535/13,59			

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
 Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
 Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A